

Vishay Siliconix

N-Channel 60 V (D-S), 175 °C MOSFET, Logic Level

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A) ^a			
60	0.0093 at V _{GS} = 10 V	50			
	0.0122 at V _{GS} = 4.5 V	50			

TO-252

Top View

Ordering Information:

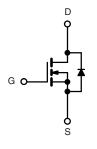
SUD50N06-09L-E3 (Lead (Pb)-free)

Drain Connected to Tab

FEATURES

- 175 °C Junction Temperature
- TrenchFET[®] Power MOSFET
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C =$	= 25 °C, unless othe	rwise noted)			
Parameter	Symbol	Limit	Unit		
Gate-Source Voltage		V _{GS}	± 20	V	
	T _C = 25 °C	1	50		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 100 °C	I _D	50 ^a		
Pulsed Drain Current	I _{DM}	100	А		
Continuous Source Current (Diode Conduction)		۱ _S	50 ^a		
Avalanche Current	I _{AS}	50	1		
Single Avalanche Energy (Duty Cycle \leq 1 %)	L = 0.1 mH	E _{AS}	125	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	136	w	
Maximum Fower Dissipation	T _A = 25 °C	' D	3 ^b , 8.3 ^{b, c}	vv	
Operating Junction and Storage Temperature Range	·	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marian and han the Amelianta	t ≤ 10 sec	R _{thJA}	15	18		
Maximum Junction-to-Ambient ^a	Steady State		40	50	°C/W	
Maximum Junction-to-Case	•	R _{thJC}	0.85	1.1		

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. $t \leq$ 10 s.

SUD50N06-09L

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static			1		1 1		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	60			v	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1	2	3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			50 μΑ		
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$			250	1	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			Α	
		V _{GS} = 10 V, I _D = 20 A	0.0074		0.0093		
		V_{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.0160		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V_{GS} = 10 V, I _D = 20 A, T _J = 175 °C			0.0200	Ω	
		V _{GS} = 4.5 V, I _D = 15 A			0.0122		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		60		S	
Dynamic	•						
Input Capacitance	C _{iss}			2650		pF	
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		470			
Reverse Transfer Capacitance	C _{rss}			225			
Total Gate Charge ^c	Qg			47	70	nC	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 50 A		10			
Gate-Drain Charge ^c	Q _{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.6 Ω		15	25	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$\text{I}_\text{D}\cong$ 50 A, V_GEN = 10 V, R_g = 2.5 Ω		35	50		
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Cha	racteristics (T _C = 25 °C)					
Pulsed Current	I _{SM}				100	А	
Diode Forward Voltage	V _{SD}	$I_{F} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		1	1.5	V	
		I _F = 20 A, di/dt = 100 A/μs					

Notes:

a. For design aid only; not subject to production testing.

b. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



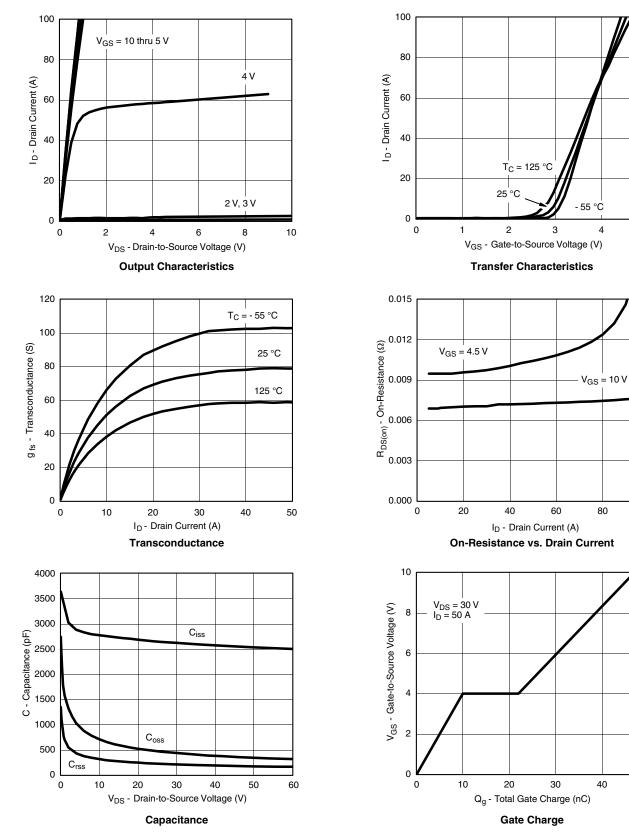
SUD50N06-09L

Vishay Siliconix

5

100

TYPICAL CHARACTERISTICS (25 °C unless noted)



For technical questions, contact: pmostechsupport@vishay.com

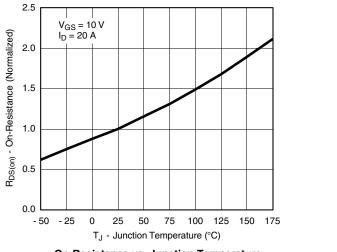
50

3

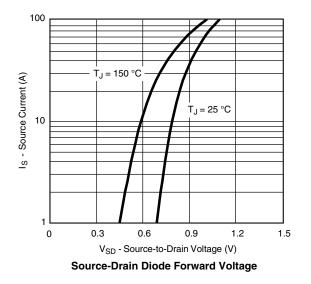
VISHAY,

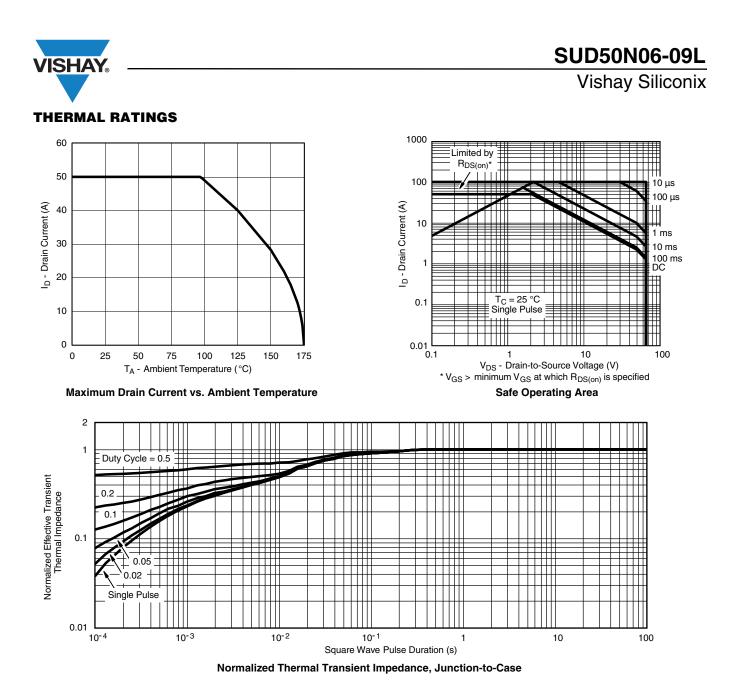
Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C unless noted)



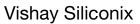
On-Resistance vs. Junction Temperature





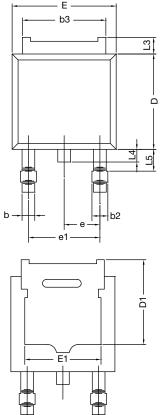
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72004.

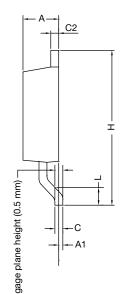
5





TO-252AA Case Outline





	MILLIN	IETERS	INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
А	2.18	2.38	0.086	0.094		
A1	-	0.127	-	0.005		
b	0.64	0.88	0.025	0.035		
b2	0.76	1.14	0.030	0.045		
b3	4.95	5.46	0.195	0.215		
С	0.46	0.61	0.018	0.024		
C2	0.46	0.89	0.018	0.035		
D	5.97	6.22	0.235	0.245		
D1	4.10	-	0.161	-		
Е	6.35	6.73	0.250	0.265		
E1	4.32	-	0.170	-		
Н	9.40	10.41	0.370	0.410		
е	2.28	BSC	0.090 BSC			
e1	4.56	BSC	0.180	BSC		
L	1.40	1.78	0.055	0.070		
L3	0.89	1.27	0.035	0.050		
L4	-	1.02	-	0.040		
L5	1.01	1.52	0.040	0.060		
ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347						

Notes

• Dimension L3 is for reference only.



Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay: SUD50N06-09L SUD50N06-09L-E3